Infineon Technologies - XE162FM24F80LAAFXUMA1 Datasheet

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	40
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	PG-LQFP-64-13
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe162fm24f80laafxuma1

Edition 2011-07

Published by
Infineon Technologies AG
81726 Munich, Germany

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16-Bit

Architecture

XE162FM, XE162HM

16-Bit Single-Chip
Real Time Signal Controller
XE166 Family / Base Line

Data Sheet

V2.1 2011-07

Microcontrollers

8 Kbytes of on-chip Stand-By SRAM (SBRAM) provide storage for system-relevant user data that must be preserved while the major part of the device is powered down. The SBRAM is accessed via a specific interface and is powered in domain M.

1024 bytes (2 × 512 bytes) of the address space are reserved for the Special Function Register areas (SFR space and ESFR space). SFRs are word-wide registers which are used to control and monitor functions of the different on-chip units. Unused SFR addresses are reserved for future members of the XE166 Family. In order to ensure upward compatibility they should either not be accessed or written with zeros.

The on-chip Flash memory stores code, constant data, and control data. The on-chip Flash memory consists of 1 module of 64 Kbytes (preferably for data storage) and modules with a maximum capacity of 256 Kbytes each. Each module is organized in sectors of 4 Kbytes.
The uppermost 4-Kbyte sector of segment 0 (located in Flash module 0) is used internally to store operation control parameters and protection information.

Note: The actual size of the Flash memory depends on the chosen device type.

Each sector can be separately write protected1), erased and programmed (in blocks of 128 Bytes). The complete Flash area can be read-protected. A user-defined password sequence temporarily unlocks protected areas. The Flash modules combine 128-bit read access with protected and efficient writing algorithms for programming and erasing. Dynamic error correction provides extremely high read data security for all read access operations. Access to different Flash modules can be executed in parallel.
For Flash parameters, please see **Section 4.5**.

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).
The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.
The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.

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1) To save control bits, sectors are clustered for protection purposes, they remain separate for programming/erasing.

3.5 Interrupt System

The architecture of the XE162xM supports several mechanisms for fast and flexible response to service requests; these can be generated from various sources internal or external to the microcontroller. Any of these interrupt requests can be programmed to be serviced by the Interrupt Controller or by the Peripheral Event Controller (PEC).

Where in a standard interrupt service the current program execution is suspended and a branch to the interrupt vector table is performed, just one cycle is 'stolen' from the current CPU activity to perform a PEC service. A PEC service implies a single byte or word data transfer between any two memory locations with an additional increment of either the PEC source pointer, the destination pointer, or both. An individual PEC transfer counter is implicitly decremented for each PEC service except when performing in the continuous transfer mode. When this counter reaches zero, a standard interrupt is performed to the corresponding source-related vector location. PEC services are particularly well suited to supporting the transmission or reception of blocks of data. The XE162xM has eight PEC channels, each whith fast interrupt-driven data transfer capabilities.

With a minimum interrupt response time of 7/11¹⁾ CPU clocks, the XE162xM can react quickly to the occurrence of non-deterministic events.

Interrupt Nodes and Source Selection

The interrupt system provides 96 physical nodes with separate control register containing an interrupt request flag, an interrupt enable flag and an interrupt priority bit field. Most interrupt sources are assigned to a dedicated node. A particular subset of interrupt sources shares a set of nodes. The source selection can be programmed using the interrupt source selection (ISSR) registers.

External Request Unit (ERU)

A dedicated External Request Unit (ERU) is provided to route and preprocess selected on-chip peripheral and external interrupt requests. The ERU features 4 programmable input channels with event trigger logic (ETL) a routing matrix and 4 output gating units (OGU). The ETL features rising edge, falling edge, or both edges event detection. The OGU combines the detected interrupt events and provides filtering capabilities depending on a programmable pattern match or miss.

Trap Processing

The XE162xM provides efficient mechanisms to identify and process exceptions or error conditions that arise during run-time, the so-called 'Hardware Traps'. A hardware trap causes an immediate system reaction similar to a standard interrupt service (branching

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1) Depending if the jump cache is used or not.

With its maximum resolution of 2 system clock cycles, the **GPT2 module** provides precise event control and time measurement. It includes two timers (T5, T6) and a capture/reload register (CAPREL). Both timers can be clocked with an input clock which is derived from the CPU clock via a programmable prescaler or with external signals. The counting direction (up/down) for each timer can be programmed by software or altered dynamically with an external signal on a port pin (TxEUD). Concatenation of the timers is supported with the output toggle latch (T6OTL) of timer T6, which changes its state on each timer overflow/underflow.

The state of this latch may be used to clock timer T5, and/or it may be output on pin T6OUT. The overflows/underflows of timer T6 can also be used to clock the CAPCOM2 timers and to initiate a reload from the CAPREL register.

The CAPREL register can capture the contents of timer T5 based on an external signal transition on the corresponding port pin (CAPIN); timer T5 may optionally be cleared after the capture procedure. This allows the XE162xM to measure absolute time differences or to perform pulse multiplication without software overhead.

The capture trigger (timer T5 to CAPREL) can also be generated upon transitions of GPT1 timer T3 inputs T3IN and/or T3EUD. This is especially advantageous when T3 operates in Incremental Interface Mode.

3.13 MultiCAN Module

The MultiCAN module contains independently operating CAN nodes with Full-CAN functionality which are able to exchange Data and Remote Frames using a gateway function. Transmission and reception of CAN frames is handled in accordance with CAN specification V2.0 B (active). Each CAN node can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers.

All CAN nodes share a common set of message objects. Each message object can be individually allocated to one of the CAN nodes. Besides serving as a storage container for incoming and outgoing frames, message objects can be combined to build gateways between the CAN nodes or to set up a FIFO buffer.

Note: The number of CAN nodes and message objects depends on the selected device type.

The message objects are organized in double-chained linked lists, where each CAN node has its own list of message objects. A CAN node stores frames only into message objects that are allocated to its own message object list and it transmits only messages belonging to this message object list. A powerful, command-driven list controller performs all message object list operations.

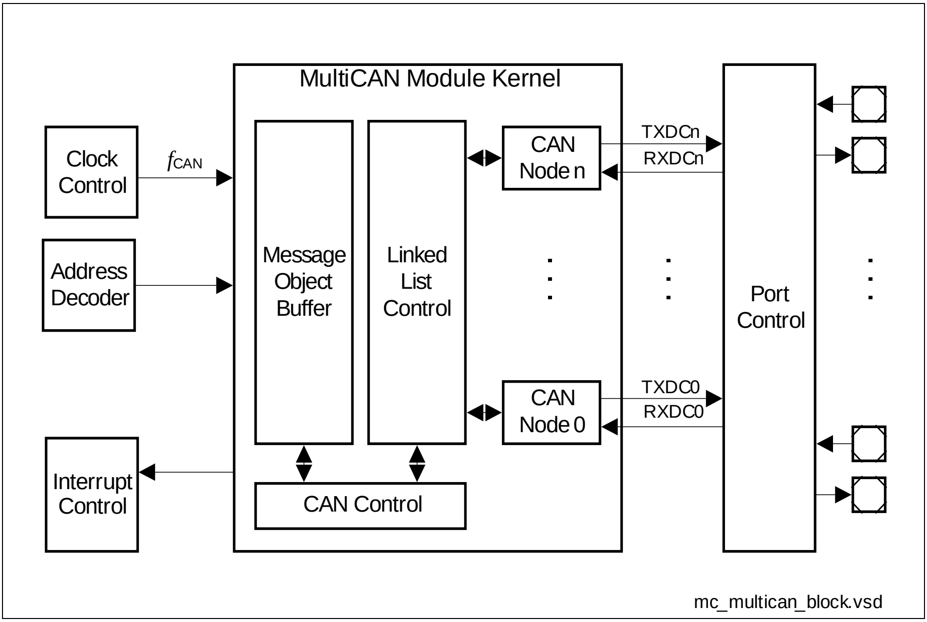

Figure 12 Block Diagram of MultiCAN Module

4.2 DC Parameters

These parameters are static or average values that may be exceeded during switching transitions (e.g. output current).

Leakage current is strongly dependent on the operating temperature and the voltage level at the respective pin. The maximum values in the following tables apply under worst case conditions, i.e. maximum temperature and an input level equal to the supply voltage.
The value for the leakage current in an application can be determined by using the respective leakage derating formula (see tables) with values from that application.

The pads of the XE162xM are designed to operate in various driver modes. The DC parameter specifications refer to the pad current limits specified in **Section 4.6.4**.

Supply Voltage Restrictions

The XE162xM can operate within a wide supply voltage range from 3.0 V to 5.5 V. However, during operation this supply voltage must remain within 10 percent of the selected nominal supply voltage. It cannot vary across the full operating voltage range.

Because of the supply voltage restriction and because electrical behavior depends on the supply voltage, the parameters are specified separately for the upper and the lower voltage range.

During operation, the supply voltages may only change with a maximum speed of dV/dt < 1 V/ms.

During power-on sequences, the supply voltages may only change with a maximum speed of dV/dt < 5 V/µs, i.e. the target supply voltage may be reached earliest after approx. 1 µs.

Note: To limit the speed of supply voltage changes, the employment of external buffer capacitors at pins V_{DDPA}/V_{DDPB} *is recommended.*

Table 13 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output Low Voltage[8]	V_{OL} CC	–	–	1.0	V	$I_{OL} \leq I_{OLmax}$
		–	–	0.4	V	$I_{OL} \leq I_{OLnom}$[9]

[1] Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

[2] Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

[3] If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

[4] The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \text{ x } e^{(1.5 + 0.028 \text{ x } TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

[5] Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} \leq V_{ILmax}$ for a pullup; $V_{PIN} \geq V_{IHmin}$ for a pulldown.

[6] These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

[7] Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} \geq V_{IHmin}$ for a pullup; $V_{PIN} \leq V_{ILmax}$ for a pulldown.

[8] The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

[9] As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

Table 14 DC Characteristics for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output Low Voltage[8]	V_{OL} CC	–	–	1.0	V	$I_{OL} \leq I_{OLmax}$
		–	–	0.4	V	$I_{OL} \leq I_{OLnom}$[10]

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \text{ x } e^{(1.5 + 0.028 \text{ x } TJ>)}$ [μA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 μA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (μA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} <= V_{IL}$ for a pullup; $V_{PIN} >= V_{IH}$ for a pulldown.

6) These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

7) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} >= V_{IH}$ for a pullup; $V_{PIN} <= V_{IL}$ for a pulldown.

8) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

9) As a rule, with decreasing output current the output levels approach the respective supply level (VOL->VSS, VOH->VDDP). However, only the levels for nominal output currents are verified.

10) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

4.2.3 Power Consumption

The power consumed by the XE162xM depends on several factors such as supply voltage, operating frequency, active circuits, and operating temperature. The power consumption specified here consists of two components:

- The switching current I_S depends on the device activity
- The leakage current I_{LK} depends on the device temperature

To determine the actual power consumption, always both components, switching current I_S and leakage current I_{LK} must be added:

$I_{DDP} = I_S + I_{LK}$.

Note: The power consumption values are not subject to production test. They are verified by design/characterization.
To determine the total power consumption for dimensioning the external power supply, also the pad driver currents must be considered.

The given power consumption parameters and their values refer to specific operating conditions:

- **Active mode**:
  Regular operation, i.e. peripherals are active, code execution out of Flash.
- **Stopover mode**:
  Crystal oscillator and PLL stopped, Flash switched off, clock in domain DMP_1 stopped.

Note: The maximum values cover the complete specified operating range of all manufactured devices.
The typical values refer to average devices under typical conditions, such as nominal supply voltage, room temperature, application-oriented activity.
After a power reset, the decoupling capacitors for V_{DDIM} and V_{DDI1} are charged with the maximum possible current.

For additional information, please refer to **Section 5.2**, **Thermal Considerations**.

Note: Operating Conditions apply.

Table 15 Switching Power Consumption

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Power supply current (active) with all peripherals active and EVVRs on	I_{SACT} CC	–	10 + 0.6 x f_{SYS}[1]	10 + 1.0 x f_{SYS}[1]	mA	[2][3]
Power supply current in stopover mode, EVVRs on	I_{SSO} CC	–	0.7	2.0	mA	

[1] f_{SYS} in MHz.

Sample time and conversion time of the XE162xM's A/D converters are programmable. The timing above can be calculated using **Table 18**.
The limit values for f_{ADCI} must not be exceeded when selecting the prescaler value.

Table 18 A/D Converter Computation Table

GLOBCTR.5-0 (DIVA)	A/D Converter Analog Clock f_{ADCI}	INPCRx.7-0 (STC)	Sample Time[1] t_S
000000_B	f_{SYS}	00_H	$t_{ADCI} \times 2$
000001_B	$f_{SYS} / 2$	01_H	$t_{ADCI} \times 3$
000010_B	$f_{SYS} / 3$	02_H	$t_{ADCI} \times 4$
:	f_{SYS} / (DIVA+1)	:	$t_{ADCI} \times$ (STC+2)
111110_B	$f_{SYS} / 63$	FE_H	$t_{ADCI} \times 256$
111111_B	$f_{SYS} / 64$	FF_H	$t_{ADCI} \times 257$

[1] The selected sample time is doubled if broken wire detection is active (due to the presampling phase).

Converter Timing Example A:

Assumptions: f_{SYS} = 80 MHz (i.e. t_{SYS} = 12.5 ns), DIVA = 03_H, STC = 00_H

Analog clock f_{ADCI} = f_{SYS} / 4 = 20 MHz, i.e. t_{ADCI} = 50 ns

Sample time t_S = $t_{ADCI} \times 2$ = 100 ns

Conversion 10-bit:

$t_{C10} = 13 \times t_{ADCI} + 2 \times t_{SYS} = 13 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.675\ \mu\text{s}$

Conversion 8-bit:

$t_{C8} = 11 \times t_{ADCI} + 2 \times t_{SYS} = 11 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.575\ \mu\text{s}$

Converter Timing Example B:

Assumptions: f_{SYS} = 40 MHz (i.e. t_{SYS} = 25 ns), DIVA = 02_H, STC = 03_H

Analog clock f_{ADCI} = f_{SYS} / 3 = 13.3 MHz, i.e. t_{ADCI} = 75 ns

Sample time t_S = $t_{ADCI} \times 5$ = 375 ns

Conversion 10-bit:

$t_{C10} = 16 \times t_{ADCI} + 2 \times t_{SYS} = 16 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.25\ \mu\text{s}$

Conversion 8-bit:

$t_{C8} = 14 \times t_{ADCI} + 2 \times t_{SYS} = 14 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.10\ \mu\text{s}$

4.5 Flash Memory Parameters

The XE162xM is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XE162xM's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 22 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	4[1]		$N_{FL\_RD} \leq 1$, $f_{SYS} \leq 80$ MHz
		–	–	1[2]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq 20$ years
Flash wait states[3]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq 8$ MHz
		2	–	–		$f_{SYS} \leq 13$ MHz
		3	–	–		$f_{SYS} \leq 17$ MHz
		4	–	–		$f_{SYS} > 17$ MHz
Erase time per sector/page	t_{ER} CC	–	7[4]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{Er} \leq 1\,000$ cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	

Table 22 Flash Parameters (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Number of erase cycles	N_{Er} SR	–	–	15 000	cycles	$t_{\mathrm{RET}} \geq 5$ years; Valid for up to 64 user-selected sectors (data storage)
		–	–	1 000	cycles	$t_{\mathrm{RET}} \geq 20$ years

1) All Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

2) Flash module 3 can be erased/programmed while code is executed and/or data is read from any other Flash module.

3) Value of IMB_IMBCTRL.WSFLASH.

4) Programming and erase times depend on the internal Flash clock source. The control state machine needs a few system clock cycles. This increases the stated durations noticably only at extremely low system clock frequencies.

Access to the XE162xM Flash modules is controlled by the IMB. Built-in prefetch mechanisms optimize the performance for sequential access.

Flash access waitstates only affect non-sequential access. Due to prefetch mechanisms, the performance for sequential access (depending on the software structure) is only partially influenced by waitstates.

1) The amplitude voltage V_{AX1} refers to the offset voltage V_{OFF}. This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by V_{IX1}.

2) Overload conditions must not occur on pin XTAL1.

Note: For crystal or ceramic resonator operation, it is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimum parameters for oscillator operation.
The manufacturers of crystals and ceramic resonators offer an oscillator evaluation service. This evaluation checks the crystal/resonator specification limits to ensure a reliable oscillator operation.

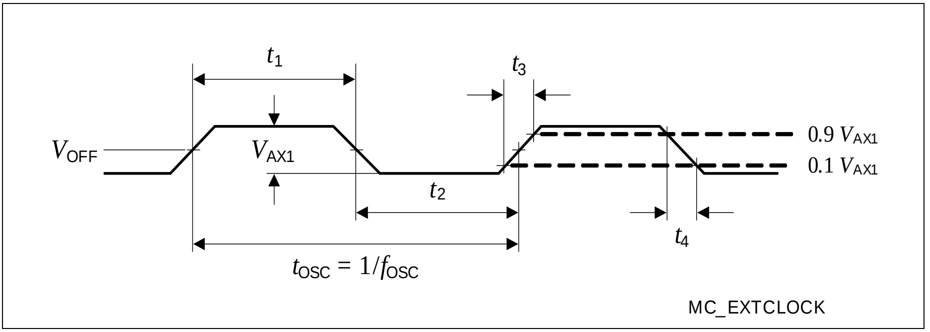

Figure 21 External Clock Drive XTAL1

4.6.4 Pad Properties

The output pad drivers of the XE162xM can operate in several user-selectable modes. Strong driver mode allows controlling external components requiring higher currents such as power bridges or LEDs. Reducing the driving power of an output pad reduces electromagnetic emissions (EME). In strong driver mode, selecting a slower edge reduces EME.

The dynamic behavior, i.e. the rise time and fall time, depends on the applied external capacitance that must be charged and discharged. Timing values are given for a capacitance of 20 pF, unless otherwise noted.

In general, the performance of a pad driver depends on the available supply voltage V_{DDP}. The following table lists the pad parameters.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

4.6.6 Debug Interface Timing

The debugger can communicate with the XE162xM either via the 2-pin DAP interface or via the standard JTAG interface.

Debug via DAP

The following parameters are applicable for communication through the DAP debug interface.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply; C_L= 20 pF.

Table 31 DAP Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
DAP0 clock period	t_{11} SR	25[1]	–	–	ns	
DAP0 high time	t_{12} SR	8	–	–	ns	
DAP0 low time	t_{13} SR	8	–	–	ns	
DAP0 clock rise time	t_{14} SR	–	–	4	ns	
DAP0 clock fall time	t_{15} SR	–	–	4	ns	
DAP1 setup to DAP0 rising edge	t_{16} SR	6	–	–	ns	pad_type= standard
DAP1 hold after DAP0 rising edge	t_{17} SR	6	–	–	ns	pad_type= standard
DAP1 valid per DAP0 clock period[2]	t_{19} CC	17	20	–	ns	pad_type= standard

[1] The debug interface cannot operate faster than the overall system, therefore $t_{11} \geq t_{SYS}$.

[2] The Host has to find a suitable sampling point by analyzing the sync telegram response.

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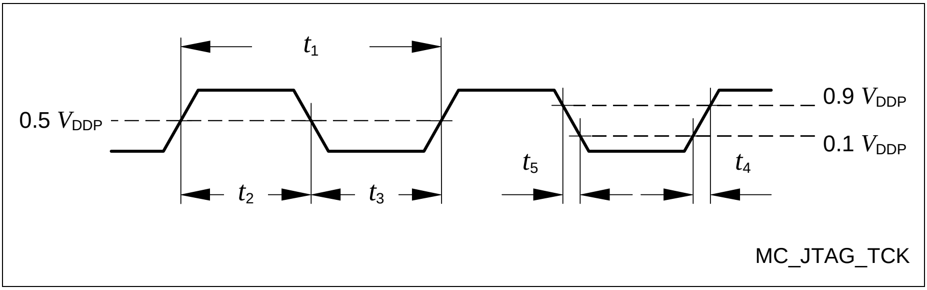

Figure 26 Test Clock Timing (TCK)

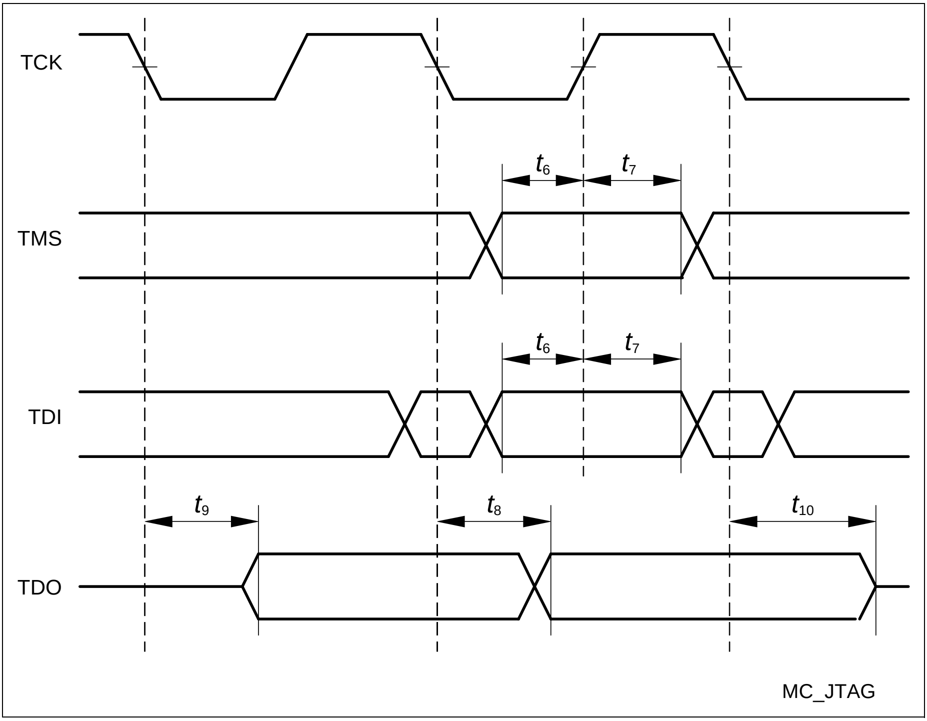

Figure 27 JTAG Timing

5.3 Quality Declarations

The operation lifetime of the XE162xM depends on the operating temperature. The life time decreases with increasing temperature as shown in **Table 37**.

Table 36 Quality Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	t_{OP} CC	–	–	20	a	See **Table 37**
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	–	–	2 000	V	EIA/JESD22-A114-B
Moisture sensitivity level	MSL CC	–	–	3	–	JEDEC J-STD-020C

Table 37 Lifetime dependency from Temperature

Operating Time	Operating Temperature
20 a	$T_J \leq$ 110°C
95 500 h	$T_J =$ 120°C
68 500 h	$T_J =$ 125°C
49 500 h	$T_J =$ 130°C
26 400 h	$T_J =$ 140°C
14 500 h	$T_J =$ 150°C